

KSA1381

PNP EPITAXIAL SILICON TRANSISTOR

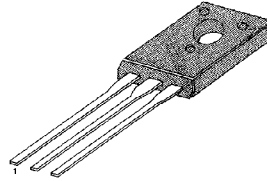
CRT DISPLAY, VIDEO OUTPUT

- High Voltage: $V_{CE0} = -300V$
- Low Reverse Transfer Capacitance: $C_{RE} = 2.3pF$ at $V_{CB} = -30V$

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	- 300	V
Collector Emitter Voltage	V_{CEO}	- 300	V
Emitter Base Voltage	V_{EBO}	- 5	V
Collector Current (DC)	I_C	- 100	mA
Collector Current (Pulse)	I_C	- 200	mA
Collector Dissipation ($T_C=25^\circ C$)	P_C	7	W
Collector Dissipation ($T_A=25^\circ C$)	P_C	1.2	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	- 55 ~ 150	$^\circ C$

TO-126



1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BV_{CBO}	$I_C = -10\mu A, I_E = 0$	- 300			V
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA, I_B = 0$	- 300			V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E = -10\mu A, I_C = 0$	- 5			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = -200V, I_E = 0$			- 0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			- 0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -10V, I_C = -10mA$	40		320	
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -20mA, I_B = -2mA$			- 0.6	V
Base Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -20mA, I_B = -2mA$			- 1	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -30V, I_C = -10mA$		150		MHz
Output Capacitance	C_{OB}	$V_{CB} = -30V, f = 1MHz$		3.1		pF
Reverse Transfer Capacitance	C_{RE}	$V_{CB} = -30V, f = 1MHz$		2.3		pF

h_{FE} CLASSIFICATION

Classification	C	D	E	F
h_{FE}	40 ~ 80	60 ~ 120	100 ~ 200	160 ~ 320

FAIRCHILD
SEMICONDUCTOR™

©1999 Fairchild Semiconductor Corporation

Rev. B

